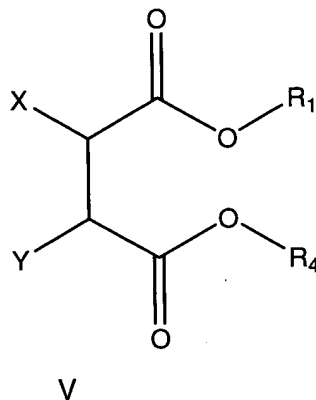
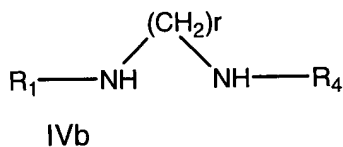
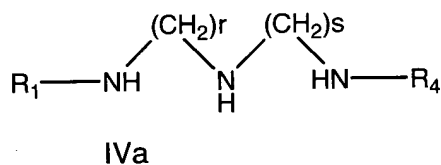
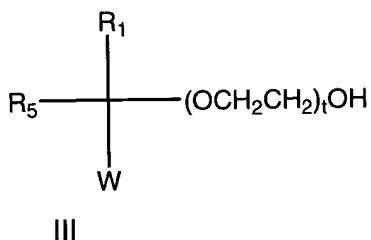


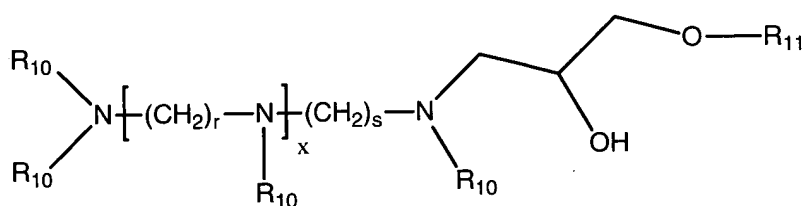
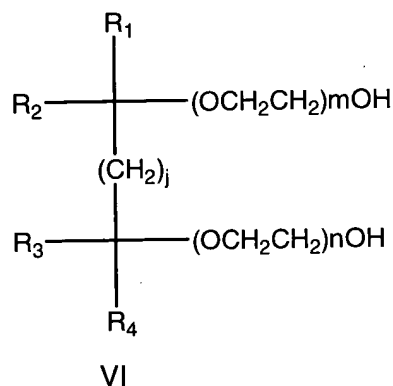
AMENDMENTS TO CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

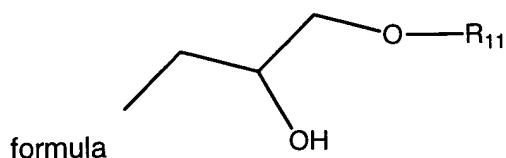
1. (Previously Presented) A method for treating a post-CMP processed substrate, the method comprising:
 - providing the post-CMP processed substrate wherein at least a portion of the substrate comprises a low dielectric constant film; and
 - contacting the substrate with a process solution comprising about 10 ppm to about 500,000 ppm of at least one surfactant having the formula (III), (IVa), (IVb), (V), (VI), (VII):





VII

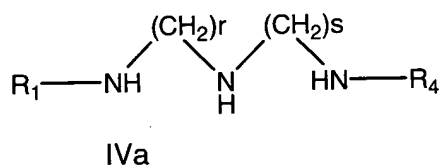
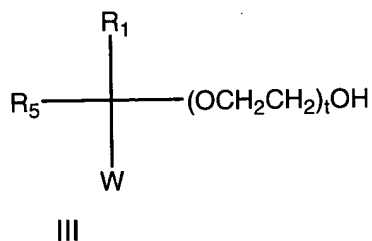
wherein R_1 and R_4 are each independently a straight or a branched alkyl group having from 3 to 10 carbon atoms; R_2 and R_3 are each independently a hydrogen atom or an alkyl group having from 1 to 5 carbon atoms; R_5 is a straight or a branched alkyl group having from 1 to 10 carbon atoms; R_{10} is independently H or a group represented by the

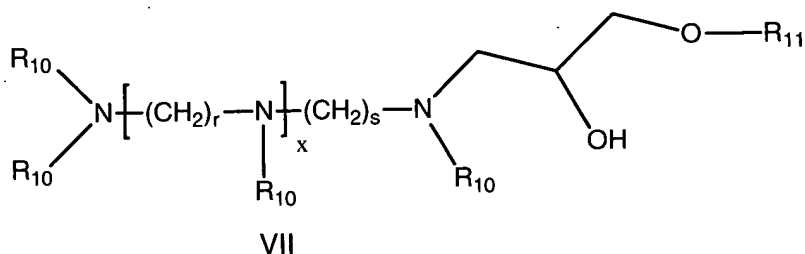
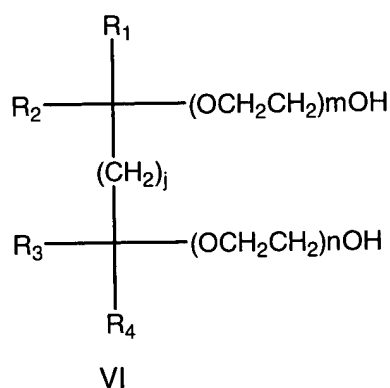
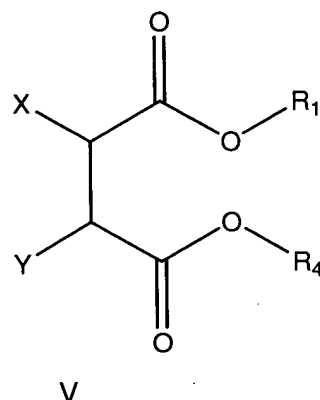
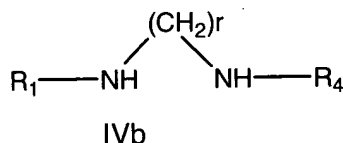


; R_{11} is a straight, branched, or cyclic alkyl group having from 4 to 22 carbon atoms; W is a hydrogen atom or an alkynyl group; X and Y are each independently a hydrogen atom or a hydroxyl group; m, n, p, and q are each independently a number that ranges from 0 to 20; r and s are each independently 2 or 3; t is a number that ranges from 0 to 2; j is a number that ranges from 1 to 5; and x is a number that ranges from 1 to 6.

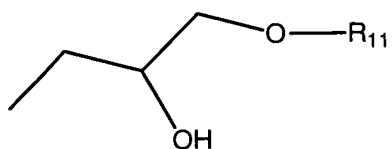
2. (Original) The method of claim 1 wherein the process solution further comprises at least one acid.
3. (Original) The method of claim 1 wherein the process solution further comprises at least one base.
4. (Original) The method of claim 1 wherein the process solution further comprises at least one oxidizing agent.

5. (Original) The method of claim 1 wherein the process solution further comprises at least one chelating agent.
6. (Original) The method of claim 1 wherein the process solution further comprises at least one corrosion inhibitor.
7. (Original) The method of claim 1 wherein the process solution further comprises an additive selected from a stabilizer, a dissolving aid, a colorant, a wetting agent, an antifoamer, a buffering agent, a second surfactant, and combinations thereof.
8. (Original) The method of claim 1 wherein the contacting step comprises a dynamic rinse.
9. (Original) The method of claim 8 wherein the process solution exhibits a dynamic surface tension of about 45 dynes/cm² or less at 23°C and 1 bubble/second according to the maximum-bubble-pressure method.
10. (Original) The method of claim 9 wherein the process solution exhibits substantially zero foam at a time greater than 60 seconds.
11. (Previously Presented) A method for treating a post-CMP processed substrate, the method comprising:
 - providing the post-CMP processed substrate wherein at least a portion of a surface of the substrate comprises a low dielectric constant film;
 - contacting the substrate with a process solution comprising at least one solvent and 10 ppm to about 500,000 ppm of at least one surfactant having the formula (III), (IVa), (IVb), (V), (VI), or (VII):





wherein R_1 and R_4 are each independently a straight or a branched alkyl group having from 3 to 10 carbon atoms; R_2 and R_3 are each independently a hydrogen atom or an alkyl group having from 1 to 5 carbon atoms; R_5 is a straight or a branched alkyl group having from 1 to 10 carbon atoms; R_{10} is independently H or a group represented by the formula



; R_{11} is a straight, branched, or cyclic alkyl group having from 4 to 22 carbon atoms; W is a hydrogen atom or an alkynyl group; X and Y are each independently a hydrogen atom or a hydroxyl group; m, n, p, and q are each independently a number that ranges from 0 to 20; r and s are each independently 2 or 3; t is a number that

ranges from 0 to 2; j is a number that ranges from 1 to 5; and x is a number that ranges from 1 to 6; and

rinsing the substrate with a deionized water rinse.

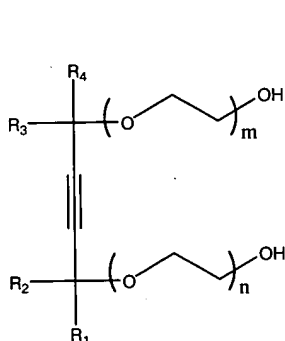
12. (Original) The method of claim 11 wherein the contacting step comprises a dynamic rinse.
13. (Original) The method of claim 11 wherein the contacting step comprises a static rinse.
14. (Original) The method of claim 11 wherein the surface of the substrate in the contacting step is wet with the deionized water rinse.
15. (Original) The method of claim 11 wherein the solvent comprises an aqueous solvent.
16. (Original) The method of claim 15 wherein the solvent comprises a non-aqueous solvent wherein the non-aqueous solvent is miscible in the aqueous solvent.
17. (Original) The method of claim 11 wherein the process solution is formed by injecting 10 to 500,000 ppm of the at least one surfactant into the solvent.
18. (Original) The method of claim 11 wherein the process stream is formed by applying 10 to 500,000 ppm of the at least one surfactant onto the surface of the substrate and applying the solvent to the substrate surface.
19. (Original) The method of claim 11 wherein the process stream is formed by passing the solvent through a cartridge comprising the at least one surfactant.
20. (Original) The method of claim 11 wherein the process stream is formed by diluting at least one surfactant with at least one solvent.
21. (Original) The method of claim 11 wherein a time of the contacting step ranges from 1 to 200 seconds.
22. (Original) The method of claim 21 wherein the time of the contacting step ranges from 1 to 150 seconds.
23. (Original) The method of claim 22 wherein the time of the contacting step ranges from 1 to 40 seconds.
24. (Original) The method of claim 11 wherein an at least one temperature of the contacting step ranges from 10 to 100°C.

Claims 25 – 33 (Cancelled)

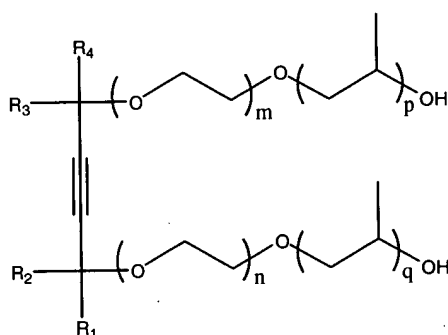
34. (Previously Presented) A method for treating a post-CMP processed substrate, the method comprising:

providing the post-CMP processed substrate comprising a semiconductor material; and

contacting the post-CMP processed substrate with a process solution consisting of a solvent selected from an aqueous solvent, a non-aqueous solvent, and combinations thereof and about 10 ppm to about 500,000 ppm of at least one surfactant having the formula (I) and (II):



I



II

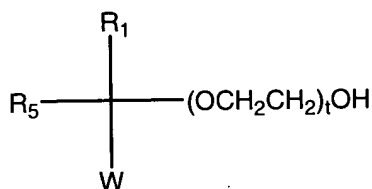
35. (Previously Presented) The method of claim 34 further comprising rinsing the post-CMP processed substrate with a deionized water rinse.

36. (Previously Presented) The method of claim 35 wherein the post-CMP processed substrate during contacting is wet with the deionized water rinse.

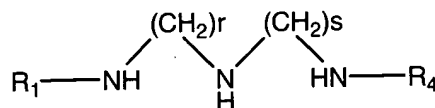
37. (Previously Presented) A method for treating a post-CMP processed substrate comprising a semiconductor material, the method comprising:

providing the post-CMP processed substrate; and

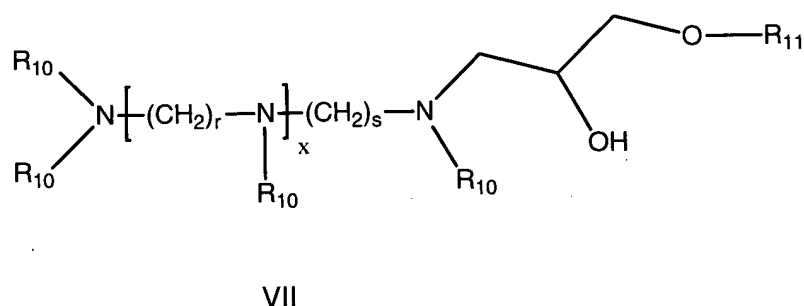
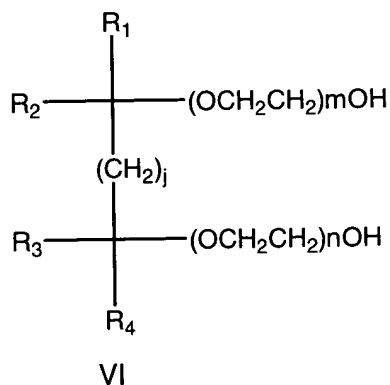
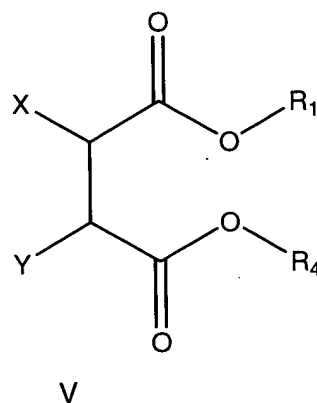
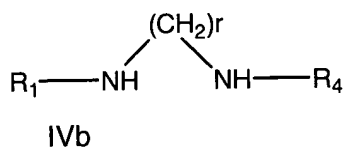
contacting the substrate with a process solution comprising about 10 ppm to about 500,000 ppm of at least one surfactant having the formula (III), (IVa), (IVb), (V), (VI), (VII):



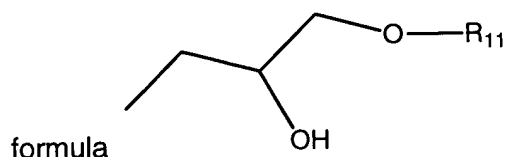
III



IVa



wherein R₁ and R₄ are each independently a straight or a branched alkyl group having from 3 to 10 carbon atoms; R₂ and R₃ are each independently a hydrogen atom or an alkyl group having from 1 to 5 carbon atoms; R₅ is a straight or a branched alkyl group having from 1 to 10 carbon atoms; R₁₀ is independently H or a group represented by the



; R₁₁ is a straight, branched, or cyclic alkyl group having from 4 to 22 carbon atoms; W is a hydrogen atom or an alkynyl group; X and Y are each independently a hydrogen atom or a hydroxyl group; m, n, p, and q are each

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independently a number that ranges from 0 to 20; r and s are each independently 2 or 3; t is a number that ranges from 0 to 2; j is a number that ranges from 1 to 5; and x is a number that ranges from 1 to 6.